

**High Power, High Voltage,
High Speed: GaN and SiC
Electrify Our World™**



GaNFast™

GeneSiC™



Up to
20x
Faster
Switching⁽¹⁾

Up to
3x
Smaller &
Lighter⁽¹⁾

Up to
40%
Energy
Savings⁽¹⁾

Up to
3x
Higher
Power Density⁽¹⁾

Up to
3x
Faster
Charging⁽¹⁾

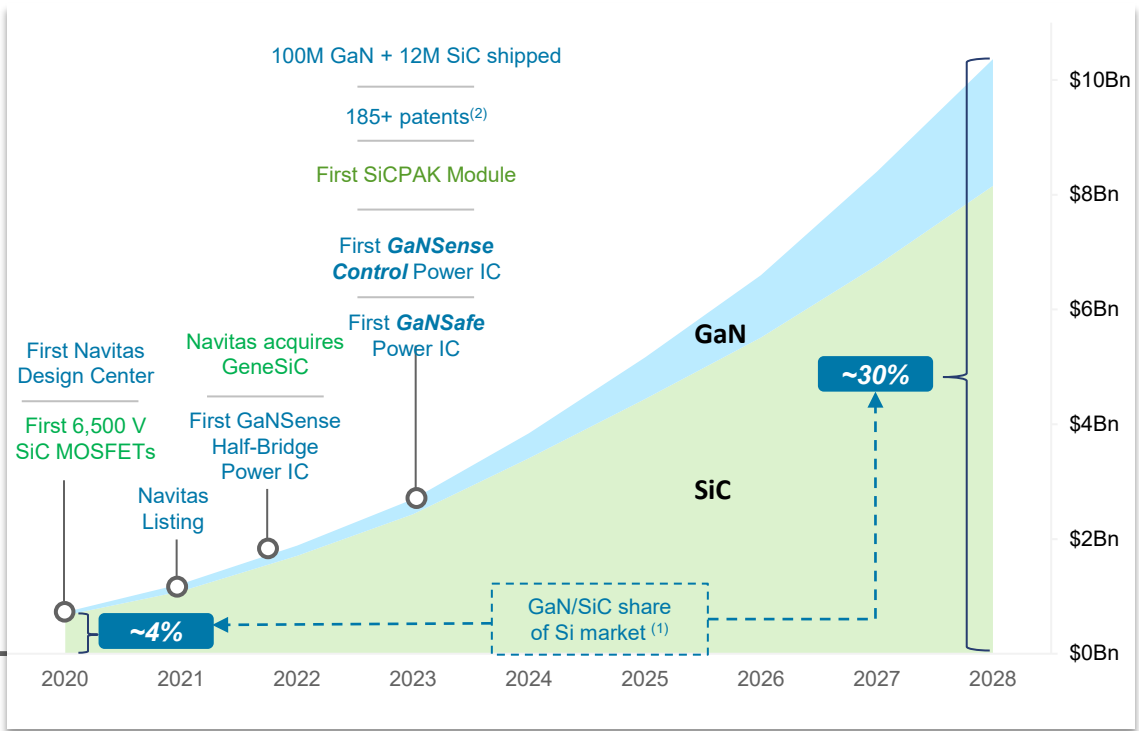
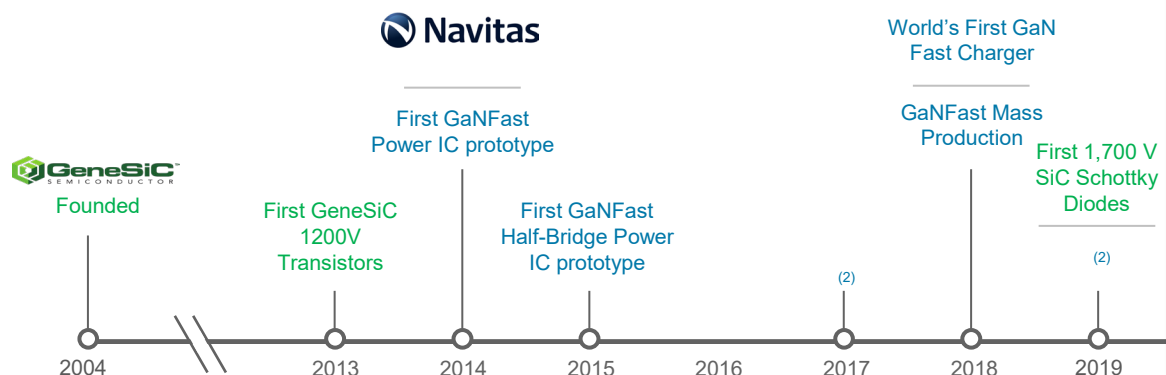
Up to
25%
Lower
System Cost⁽²⁾



GaN and SiC replacing Si in next-generation power applications

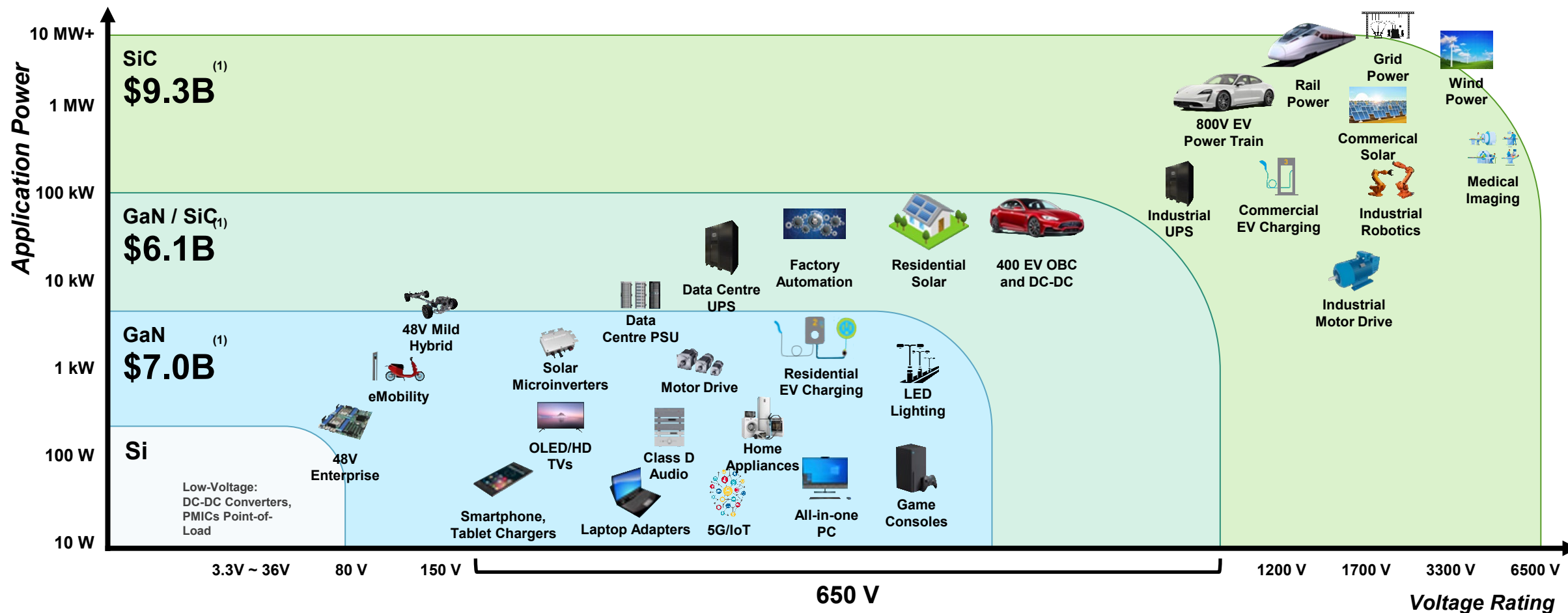
1. Statistical data is based on Navitas estimates of GaN-based systems compared to Si-based estimates in the 2024-2025 timeframe. Based on Navitas measurements of select GaN-based mobile wall chargers compared to Si-based chargers with similar output power, incl. 2019 study of 65W fast chargers, 2022 customer statement re 2.7 kW data center AC-DC
2. Navitas estimates based on customer feedback as the expected system cost saving overtime as of April 2023

Right Time, Right Technology, Right Company



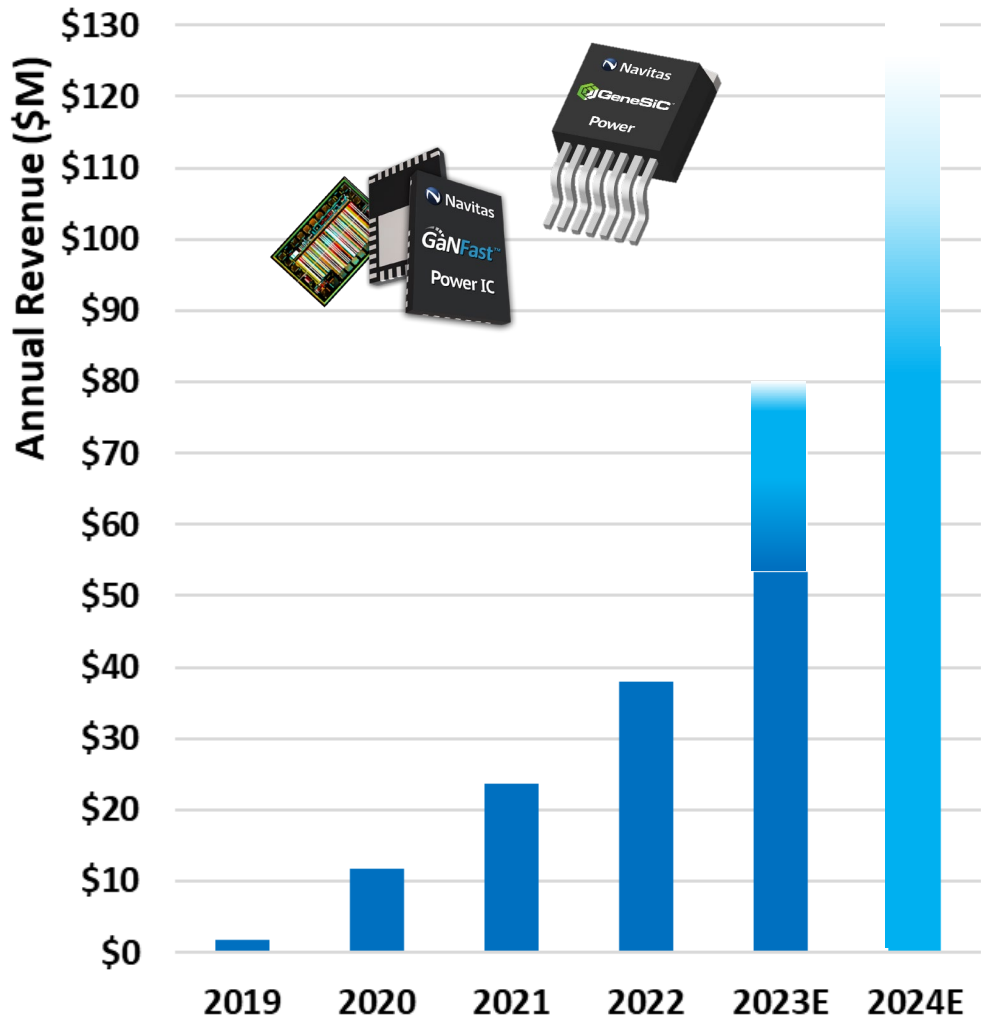
1. Estimated based on Power SiC/GaN Compound Semiconductor Market Monitor, Q1 2023, Yole Intelligence
 2. Granted or pending

Target Markets: \$22B/year



1. Navitas company estimates, potential market opportunity in 2026 is \$22B+ for GaN and SiC, replacing certain of the silicon market share. Axes not to scale

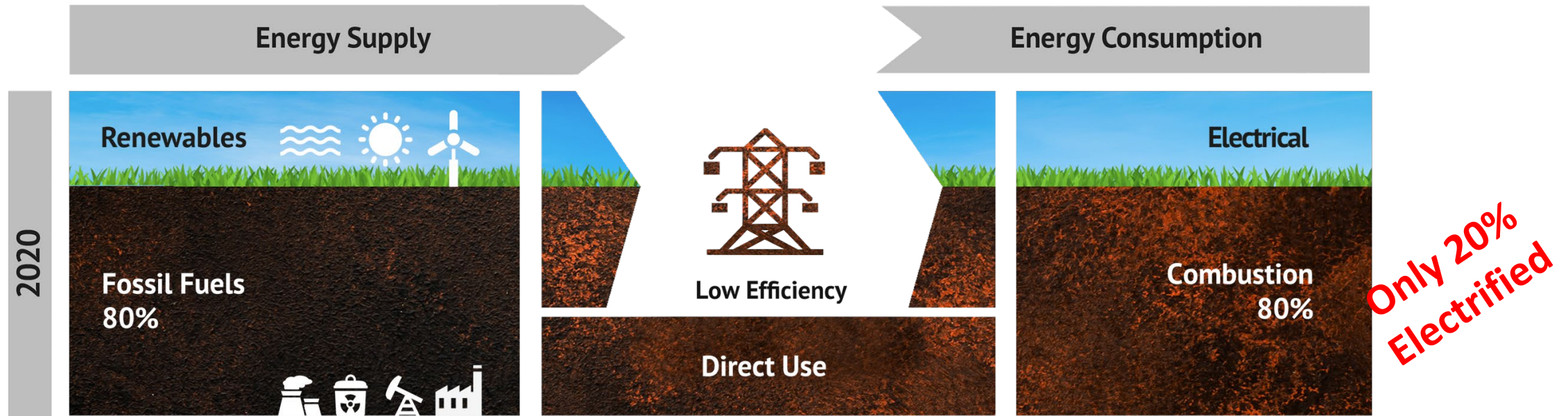
Navitas: Growing Faster than the Market

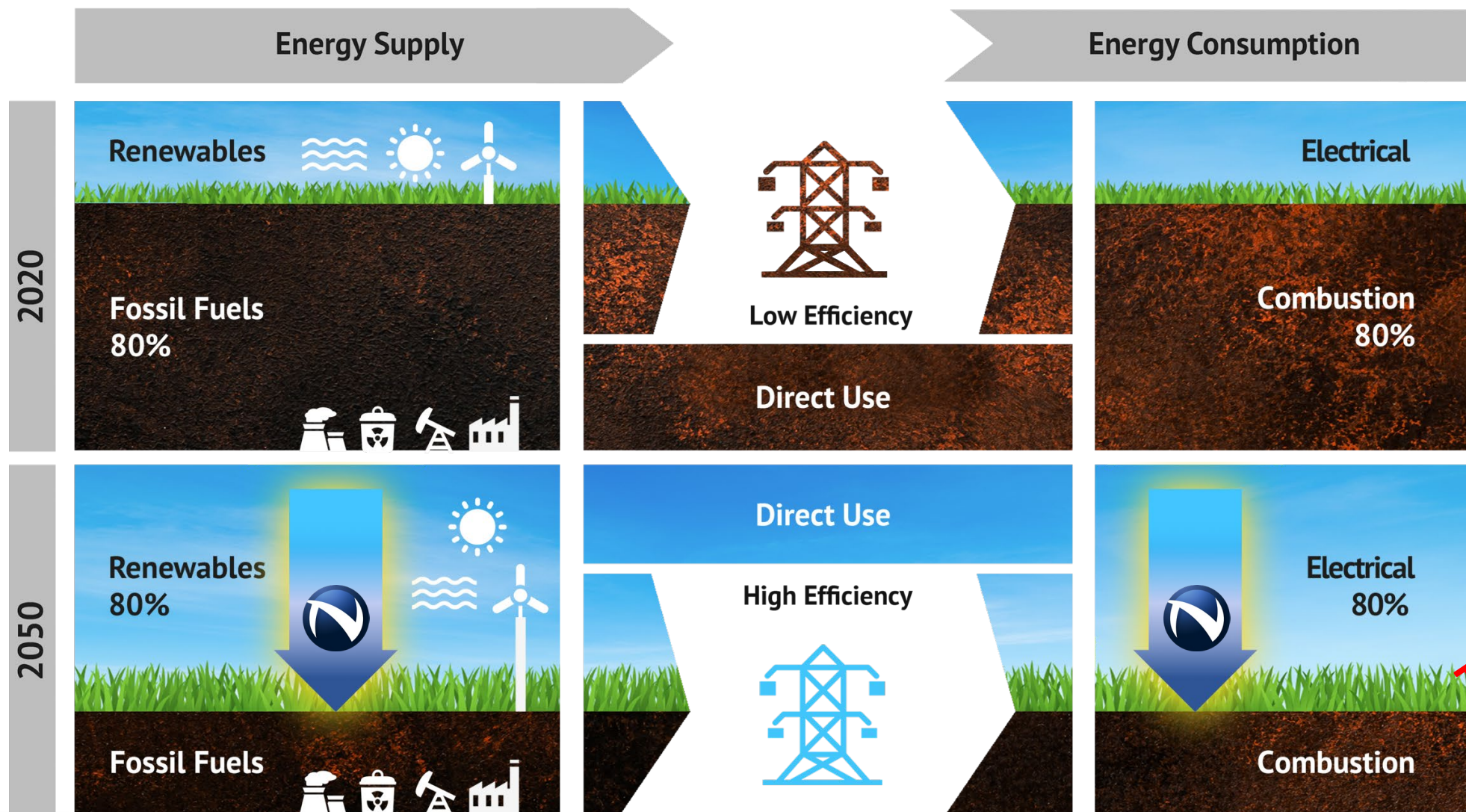


- Q3 Financial Report (November 9th, 2023)
 - Revenue \$22M (+115% yr/yr, +22% Q/Q)
 - Margin 42.1% (+3.7% yr/yr, +0.6% Q/Q)
 - Cash \$177M, no debt.
 - >\$1B customer pipeline
- Guidance:
 - Q4 \$25-\$26M, gross margin 42.5% (+/-0.3%)
 - 2023 Revenue = 2x 2022
 - 2024: “Grow at least 50%”



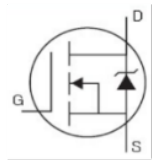
The Fossil Fuel Challenge





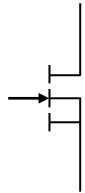
Target 80%

Discrete Silicon



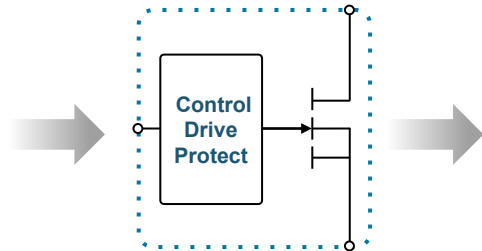
- Old
- Slow
- Low efficiency

Discrete GaN



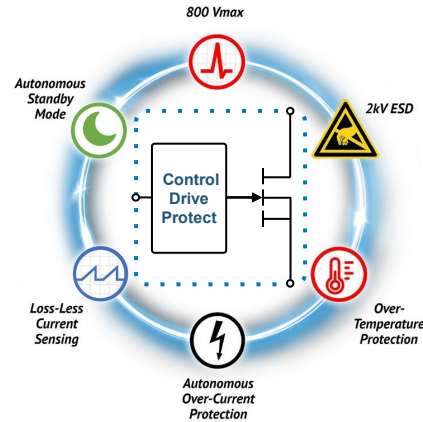
- Vulnerable
- Difficult to use
- Unknown reliability

GaNFast™



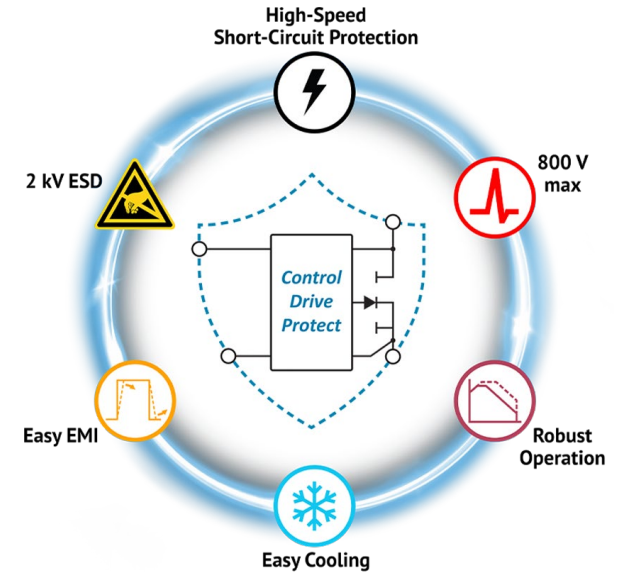
- ✓ Robust
- ✓ Easy to use
- ✓ Proven reliability

GaNSense™



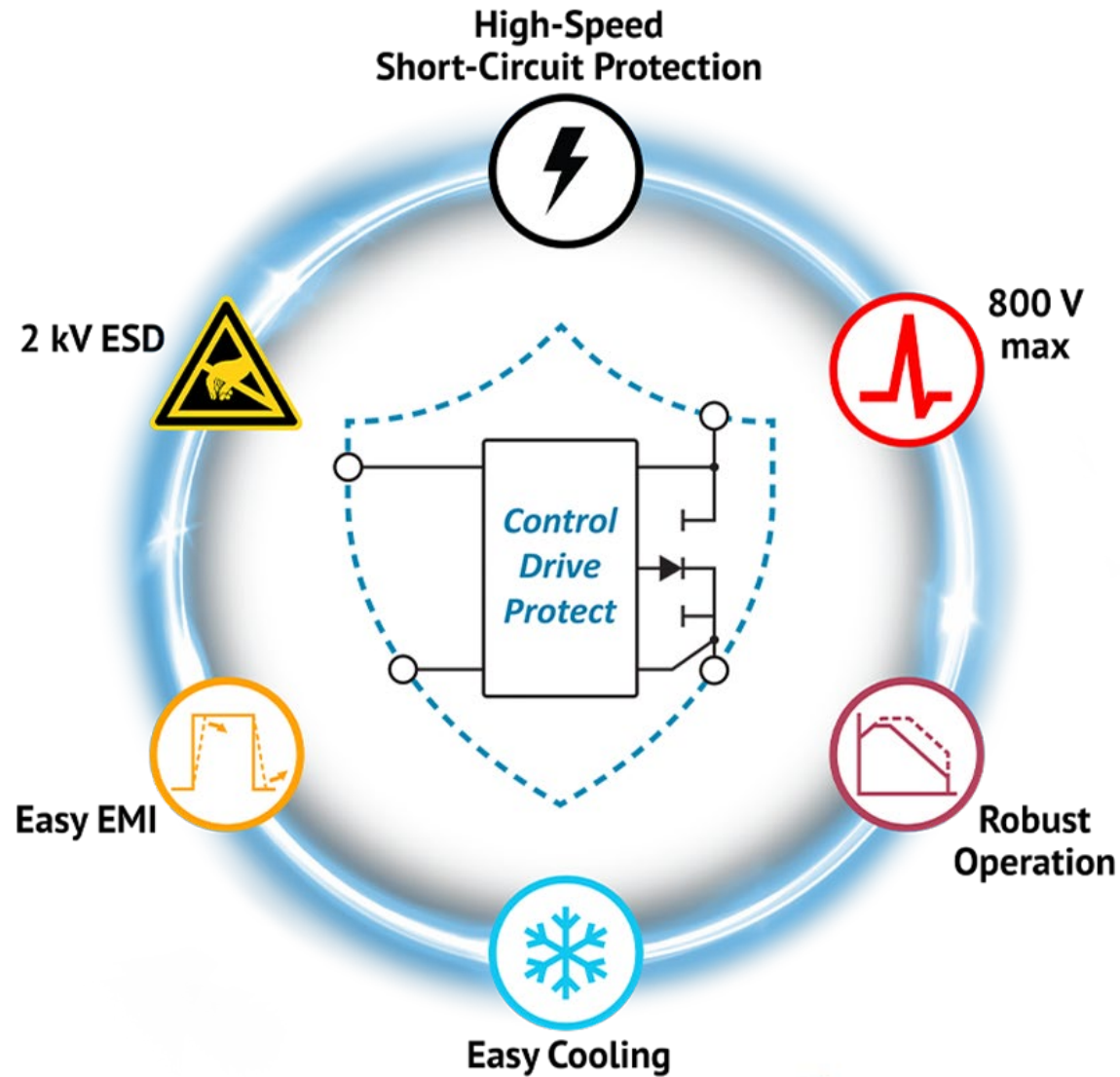
- GaNFast plus:
- ✓ Autonomous protection
 - ✓ Loss-less current sensing

GaNSafe™

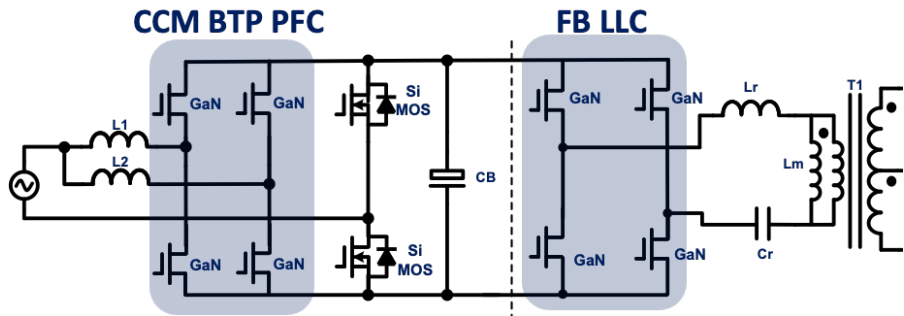


- GaNSense plus:
- ✓ Short-Circuit Detection
 - ✓ Ultra-fast autonomous protection
 - ✓ Robust, cool packaging
 - ✓ Programmable dV/dt turn-ON and OFF

Efficiency
Reliability
Speed
Integration



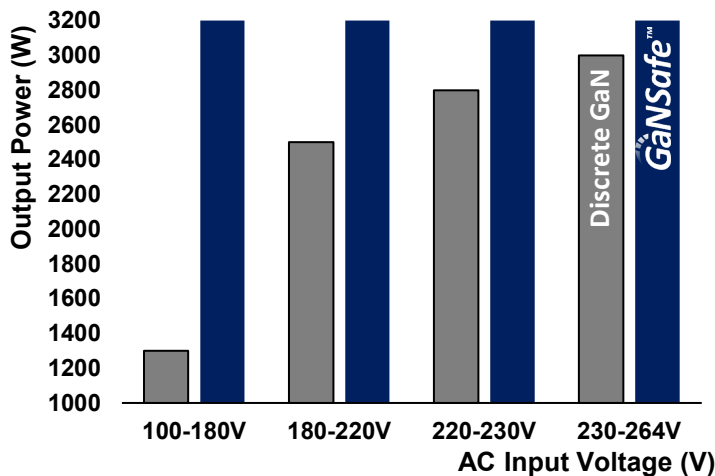
- Data center AC-DC 'silver box' (12V)
- CRPS185 form factor



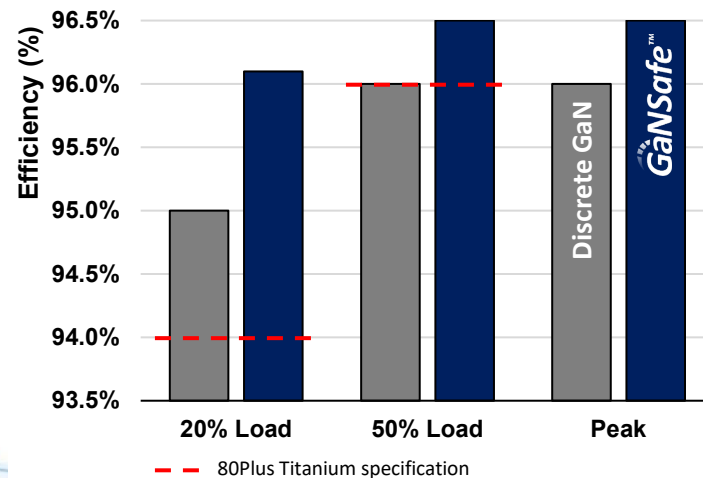
Power	2,800 W	3,200 W
PFC	8 x 32 mΩ	4 x 45 mΩ
DC-DC	4 x 32 mΩ	4 x 55 mΩ
Total	12 x GaNPX	8 x TOLL

GaNSafe™
33% fewer power components

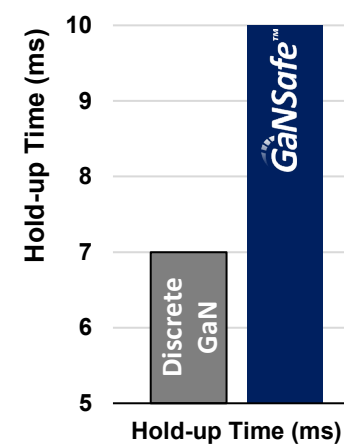
GaNSafe™ True 3,200W CRPS185



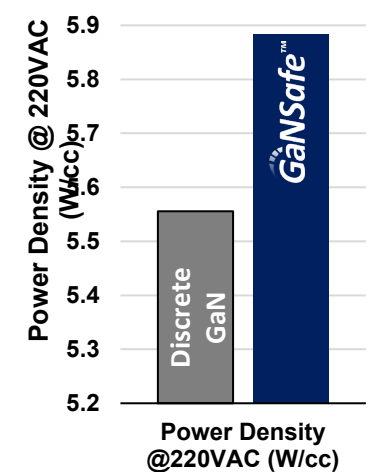
GaNSafe™ Titanium Plus, with margin



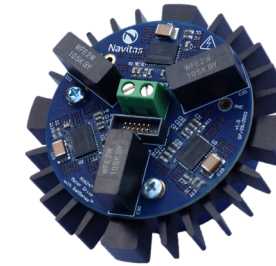
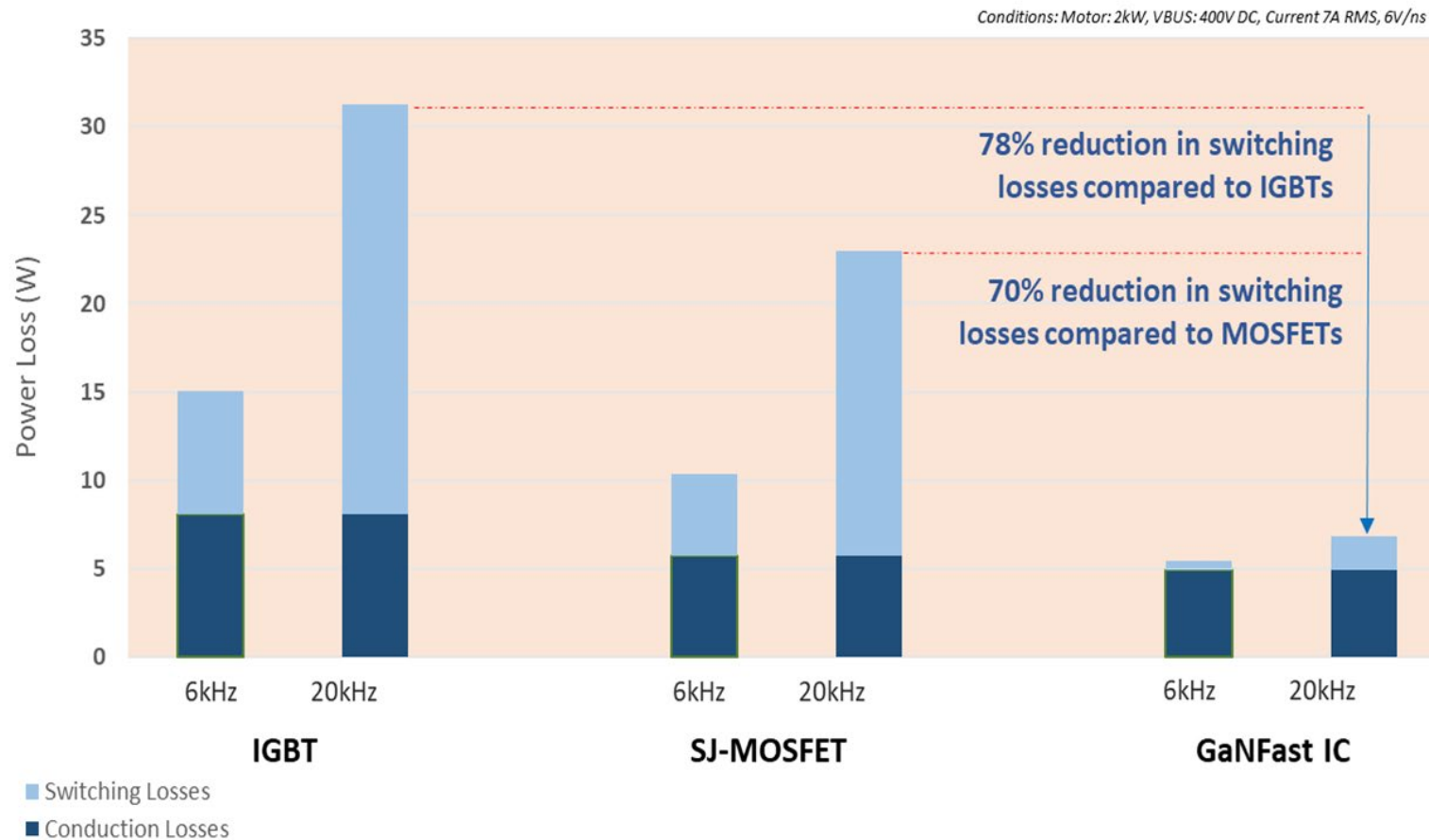
GaNSafe™ +40% Hold-up



GaNSafe™ ~100W/in³



GaN Drives Efficiency: Motor Drive Example

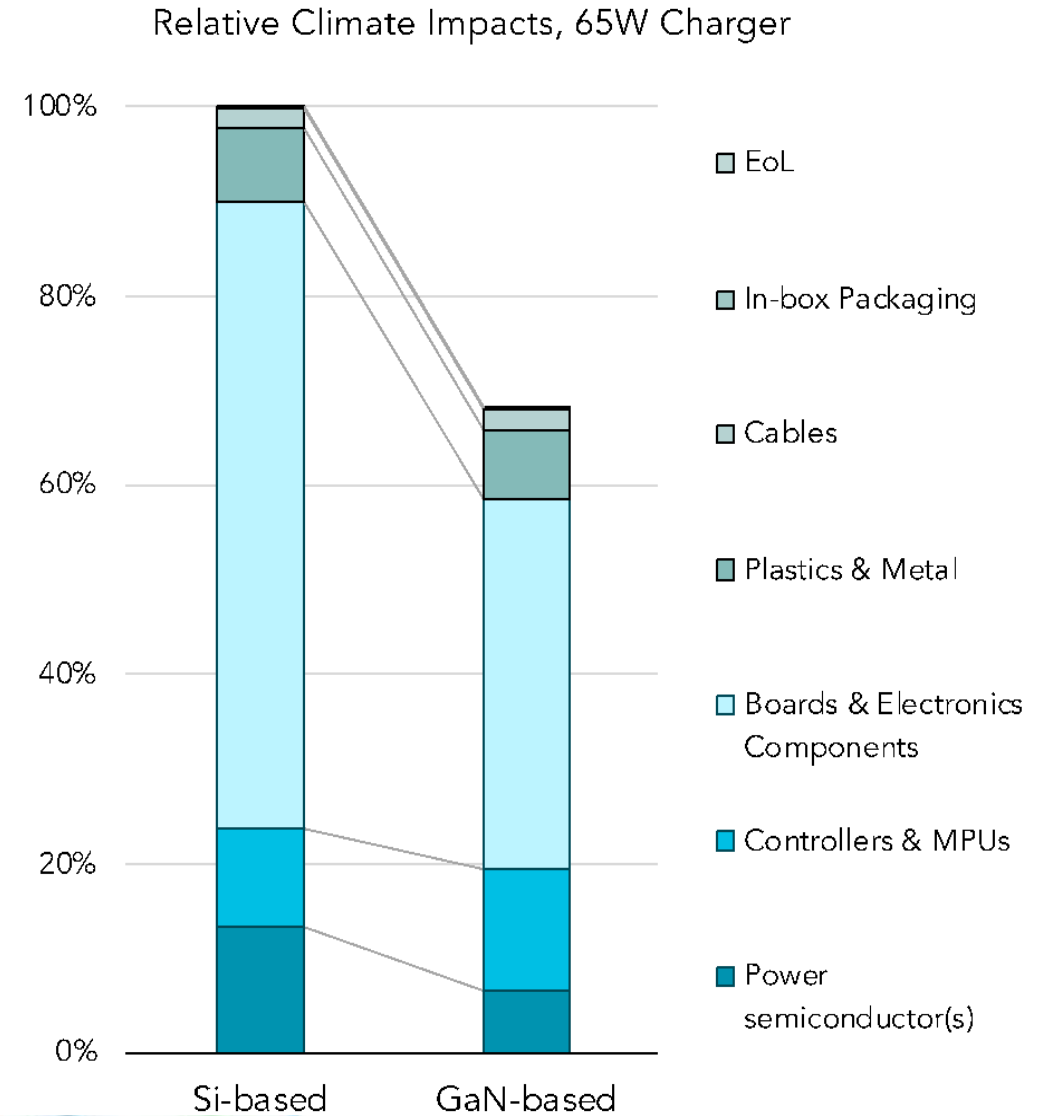
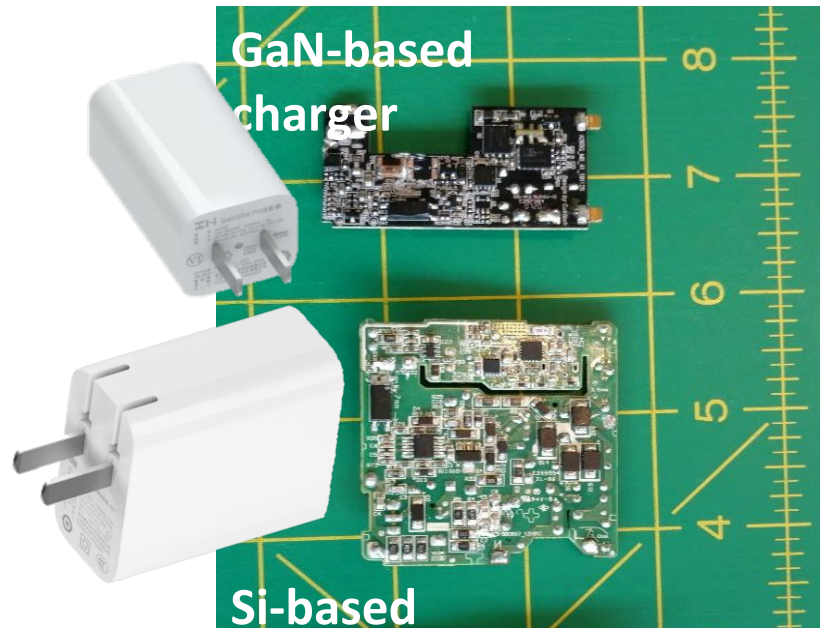


Navitas 400W
3-phase Platform
for Inverter-Motor
Integration

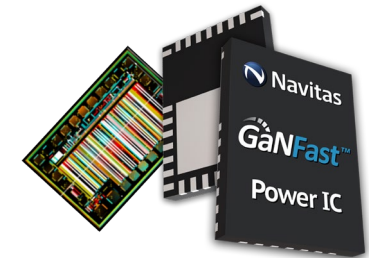
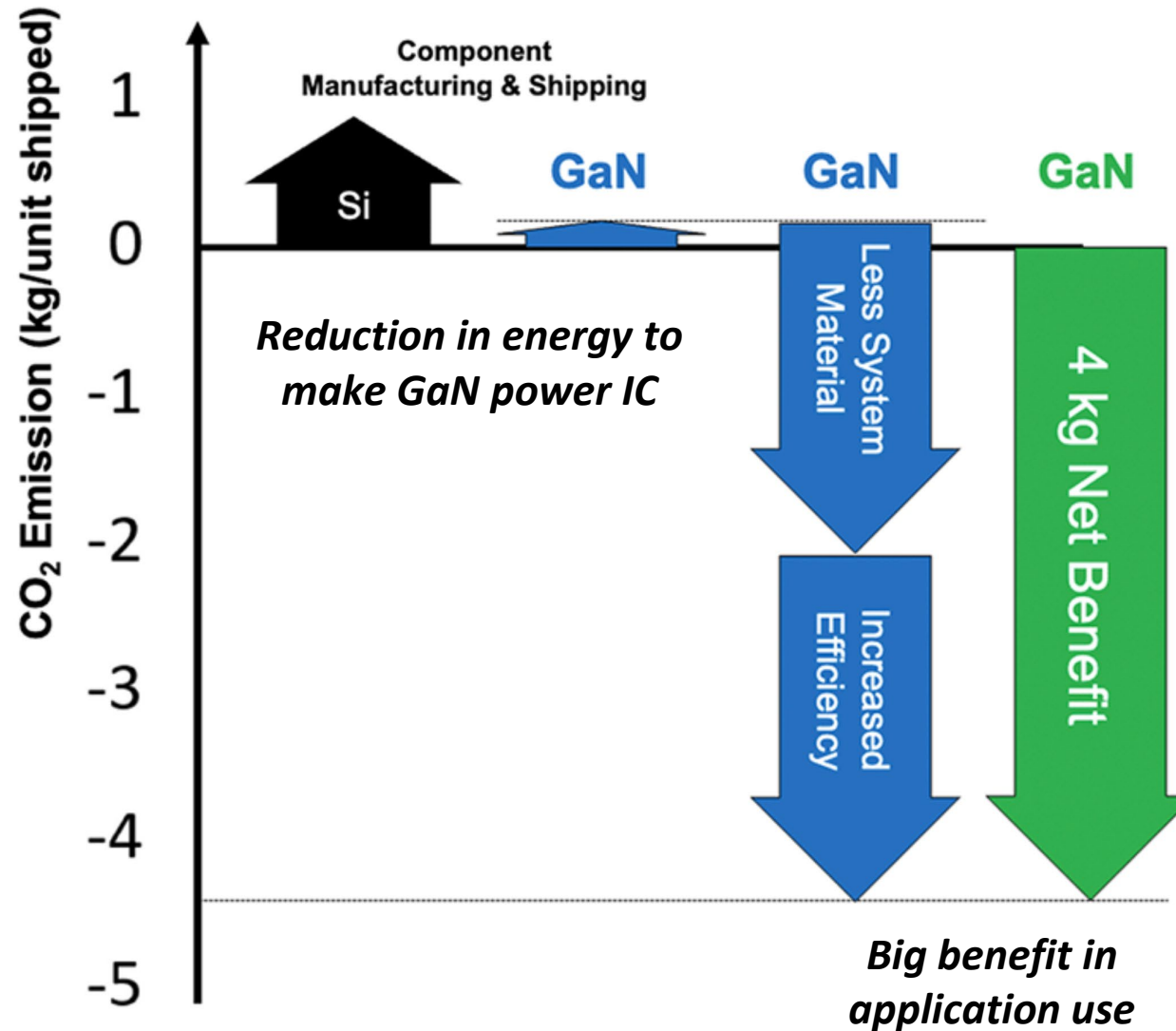
- 2x higher frequency
- >60% fewer components, PCB area
- 95-97% efficiency
- 80% energy savings vs Silicon BLDC
- 90% energy savings vs AC motors
- High reliability
- Fast time to market

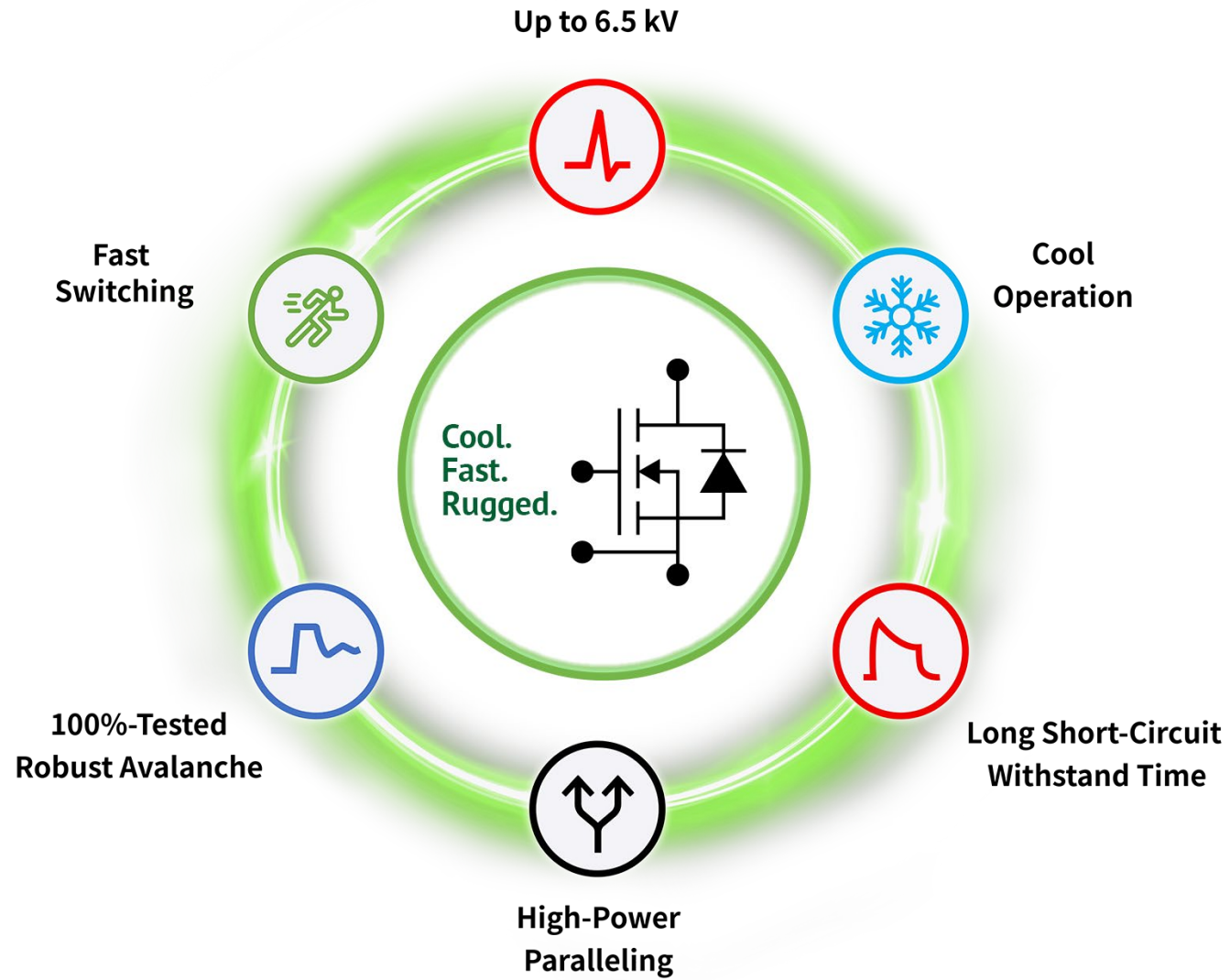
65W charger: GaN vs Si Dematerialization

- Higher frequency
= smaller
= lighter
= less material



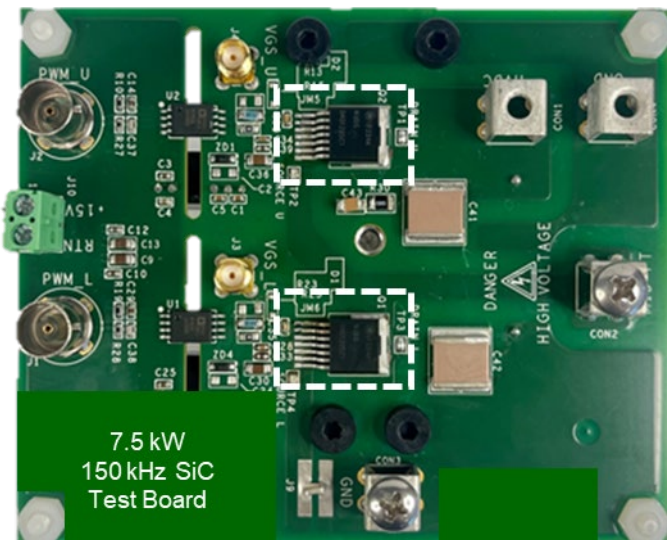
Every GaNFast Power IC Shipped Saves Over 4 kg CO₂





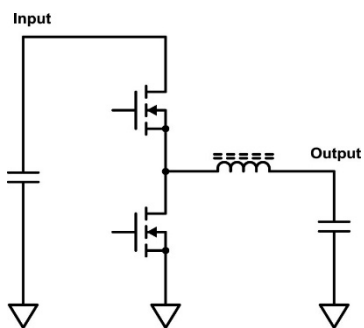
	<p>Planar</p>	<p>Trench</p>	<p>GeneSiC</p>
Manufacturability	<ul style="list-style-type: none"> » Repeatable » High yield » Low cost 	<ul style="list-style-type: none"> » Inconsistent trench etch » Lower yields » High cost 	<ul style="list-style-type: none"> » Repeatable » High yield » Low cost
Performance	<ul style="list-style-type: none"> » High $R_{DS(ON)}$ / area » Slow switching » High $R_{DS(ON)}$ / Δ temp 	<ul style="list-style-type: none"> » Lower $R_{DS(ON)}$ / area » Faster switching » High $R_{DS(ON)}$ / Δ temp 	<ul style="list-style-type: none"> » Lower $R_{DS(ON)}$ / area » Fastest switching » Lowest $R_{DS(ON)}$ / Δ temp
Reliability	<ul style="list-style-type: none"> » Rugged gate oxide (stable V_{TH}) 	<ul style="list-style-type: none"> » Failures due to non-uniform gate oxide » Lower short-circuit capability 	<ul style="list-style-type: none"> » Highest 100% tested avalanche » Long short-circuit withstand time » Rugged gate oxide (stable V_{TH})

No-Compromise Technology

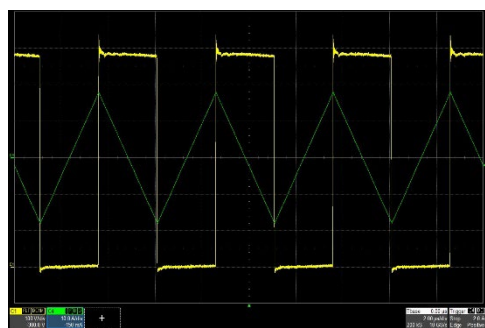


Test Board

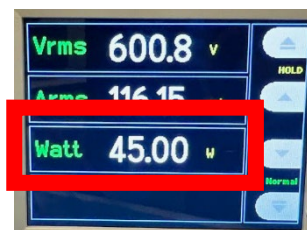
- GeneSiC trench-assisted planar FET vs. Competitor SiC FET
 - 1,200 V, 40 mΩ, D2pak in half-bridge
 - Represents 7.5 kW DC-DC converter (e.g. data center, EV)
 - 150 kHz switching = ~10x faster than Si IGBT example
- **>80% energy savings (>3,000 kWh/yr) vs Si IGBTs**
-25°C cooler = 3x longer life vs other SiC
(reduced maintenance / repair costs)



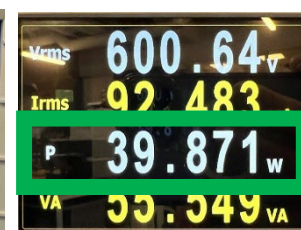
Test Circuit
(1-phase of 3-phase motor drive)



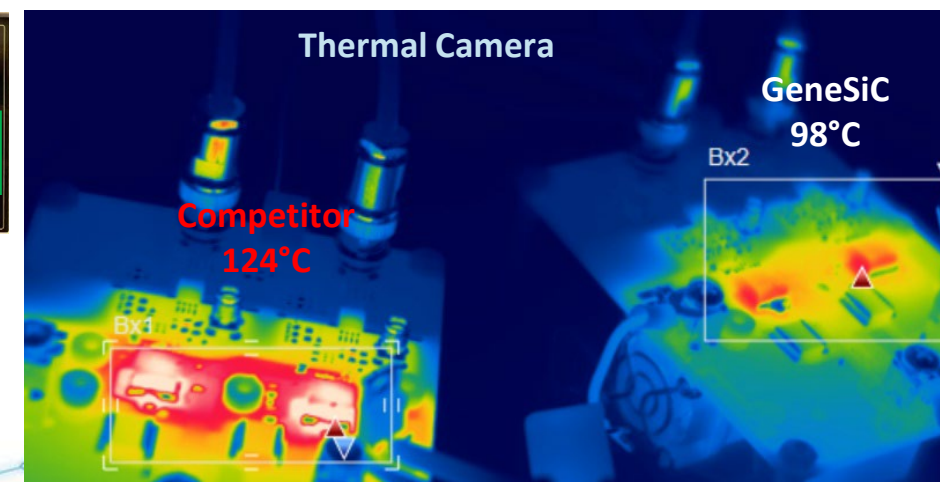
Switching Waveforms
(40 A pk-pk, 20 A turn-off)



Competitor SiC
45 W system loss



GeneSiC
40 W system loss
-30% SiC loss



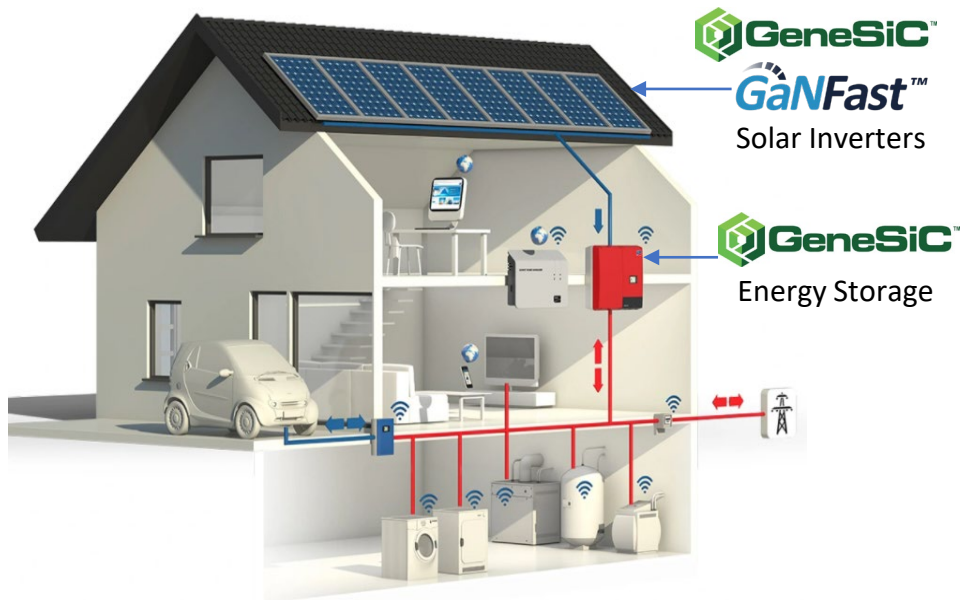


China to add 120-140 GW of solar in 2023 (+40% vs 2022)

***Expect 2x capacity, produce 1,200 GW by wind + solar by 2025
5 years ahead of target (2030)***

“Solar will soon become the most economical form of electricity in China, surpassing hydropower to become the largest non-fossil energy source by the end of this year”⁽¹⁾

(1) “Solar to jump into renewable energy driving seat at home and abroad, as China’s capacity just keeps expanding, analysts say”, South China Morning Post, 26 May, 2023



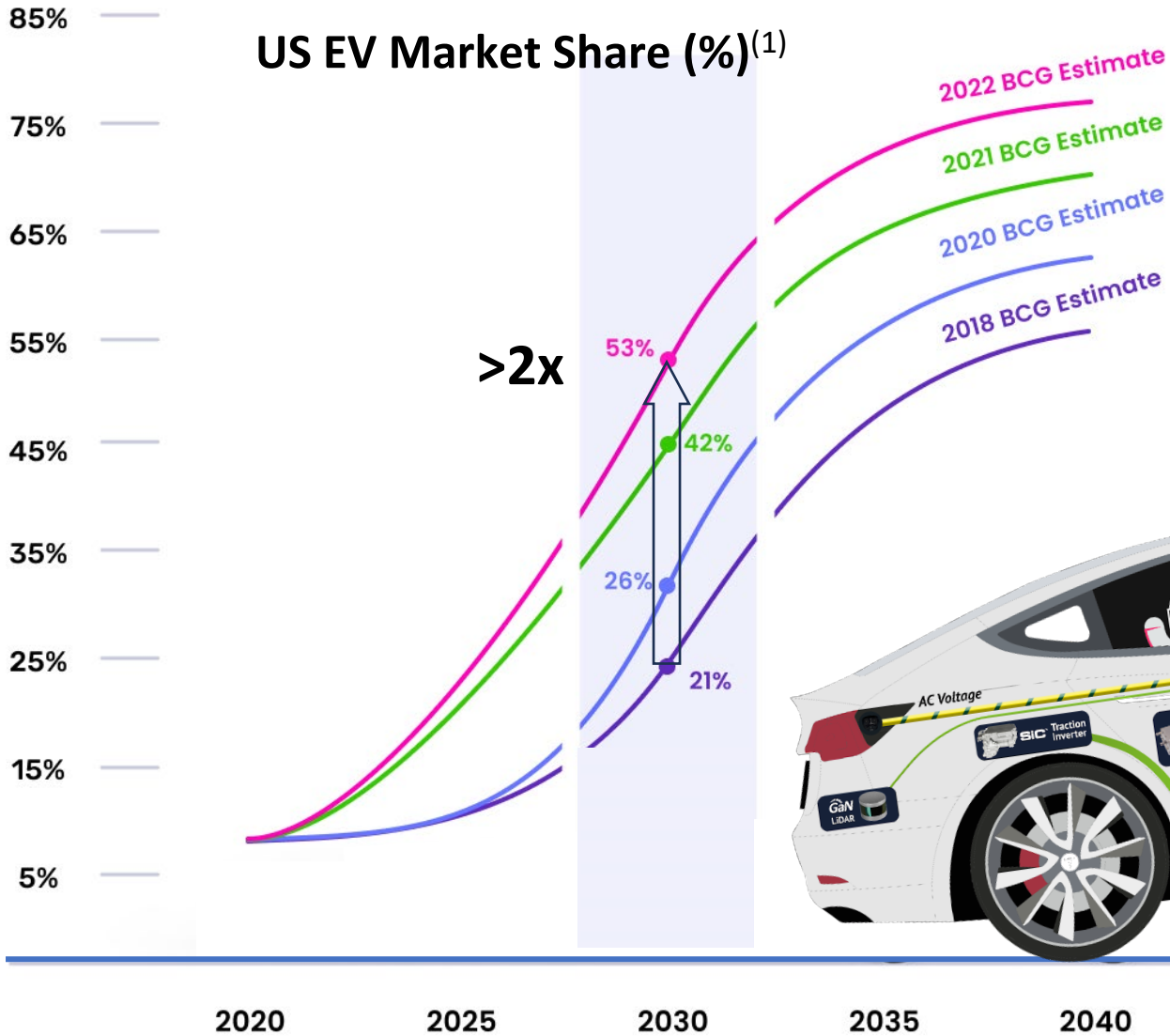
Customers in Development, Production



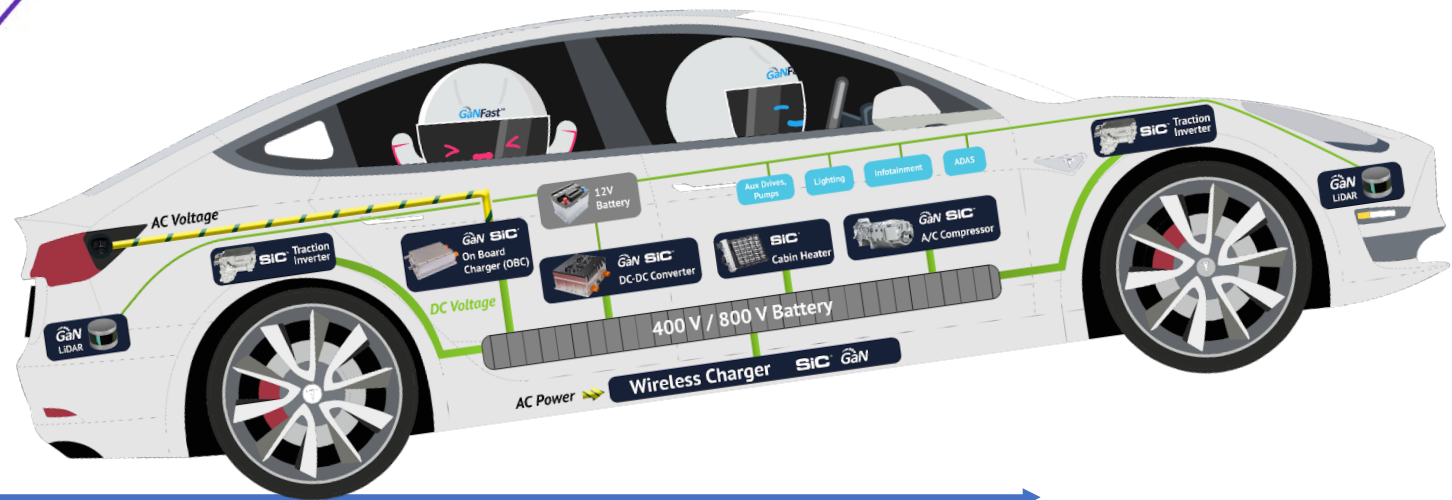
(1) Navitas est. 6.2 kW residential installation with silicon inverter at 97.5%, GaN at 98.5% efficiency. (2) Market estimates for 2030, based on DNV and Navitas analysis. (3) Per Q1'23 earnings report

Accelerating Adoption: EV

US EV Market Share (%)⁽¹⁾



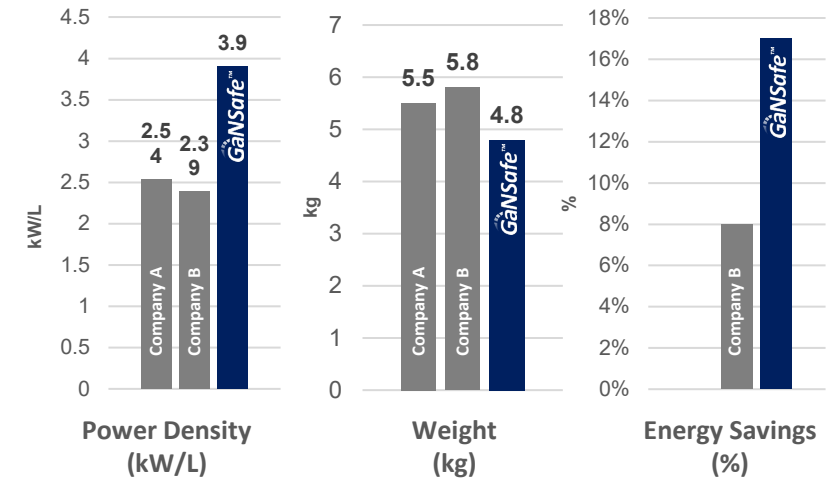
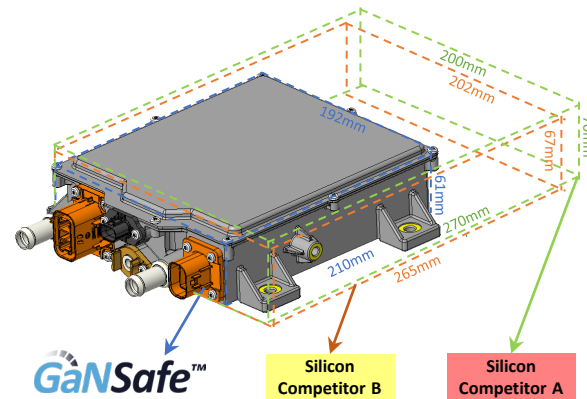
Customers in Production, Engagement⁽³⁾



(1) BCG, via <https://www.recurrentauto.com/research/ev-adoption-us> (2) Company internal estimate 2030, 30M EV/yr, based on DNV and Navitas analysis. Note: Assumes 150 kW traction inverter, 100 kWh battery, \$100/kWh battery cost and typical 230 mile range. (3) Represent select potential, engaged customers. Logos do not indicate binding long-term agreements.



GaNSafe™
Power density +50%
to 3.9 kW/litre

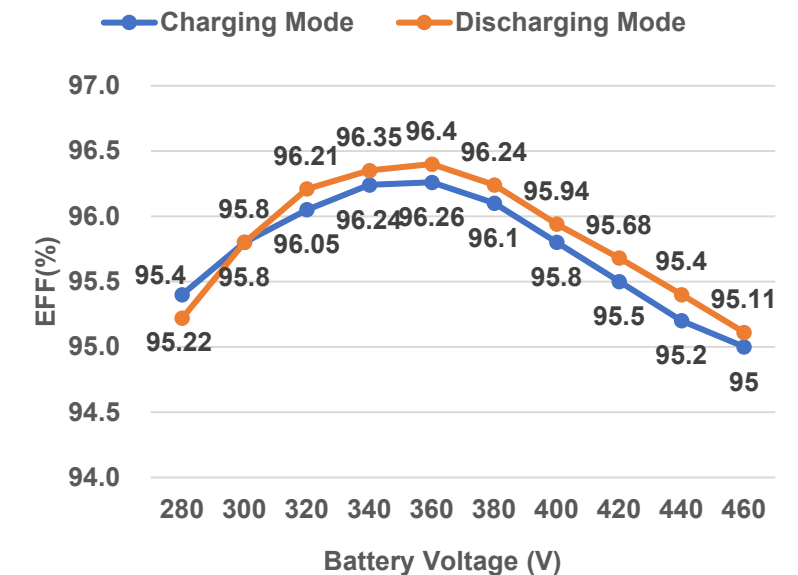
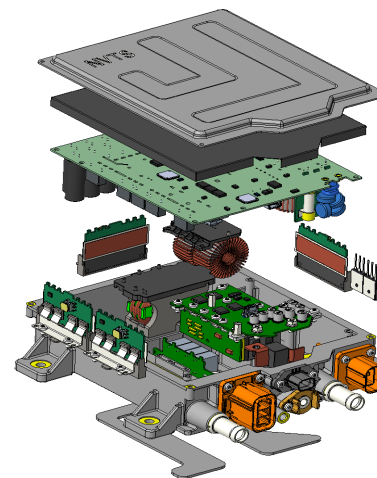


Combination 6.6 kW OBC + 3 kW DC-DC:

- AC Input: 90~265 V_{AC} up to 32 A
- DC Output: 470~860 V_{DC}, full load
- Power Output: 6.6 kW charging, 6.0 kVA discharging
- Efficiency: ≥ 95% @ Full Load
- DC-DC Output: 9~16 V_{DC}

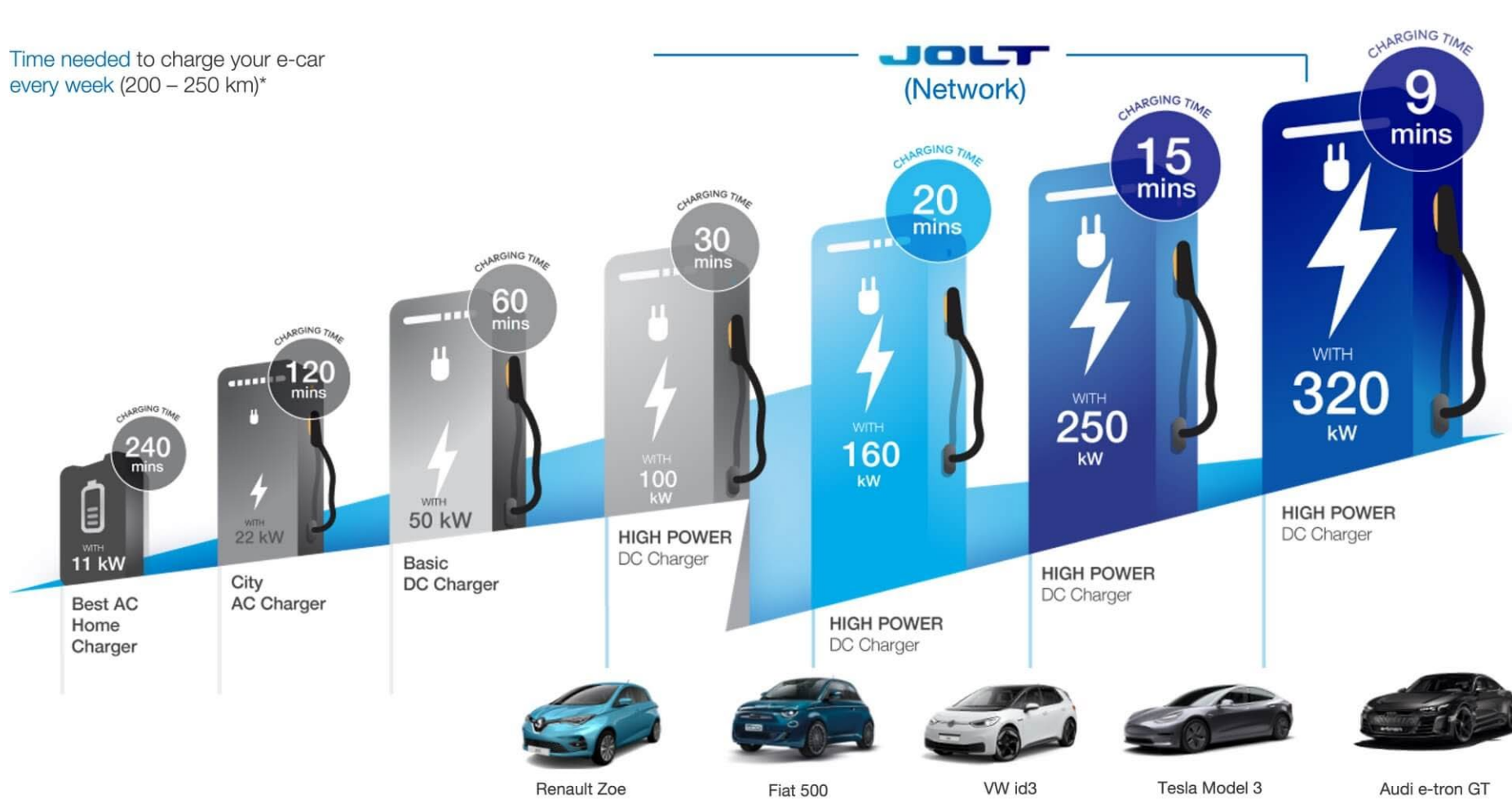
Mechanical:

- Dimensions: 210 x 192 x 61mm (≤ 2.5 litre)
- Cooling: -40 to +65°C (Cold Plate)
- Communication: IP 67, CAN Bus interface



Accelerating Charging

Time needed to charge your e-car every week (200 – 250 km)*



“10-80% charge in only 18 minutes!”⁽²⁾

Low-Power Charging
AC & 50 kW DC Chargers

High-Power Charging
All new cars can charge over 100 kW DC

(1) <https://jolt.energy/whats-the-difference-between-ac-dc-and-ultra-fast-charging/>

(2) Level 3 800V 350 kW DC charger 10-80% in 18 minutes for Genesis GV70 SUV

HV Long-Haul Trucks Need HV SiC

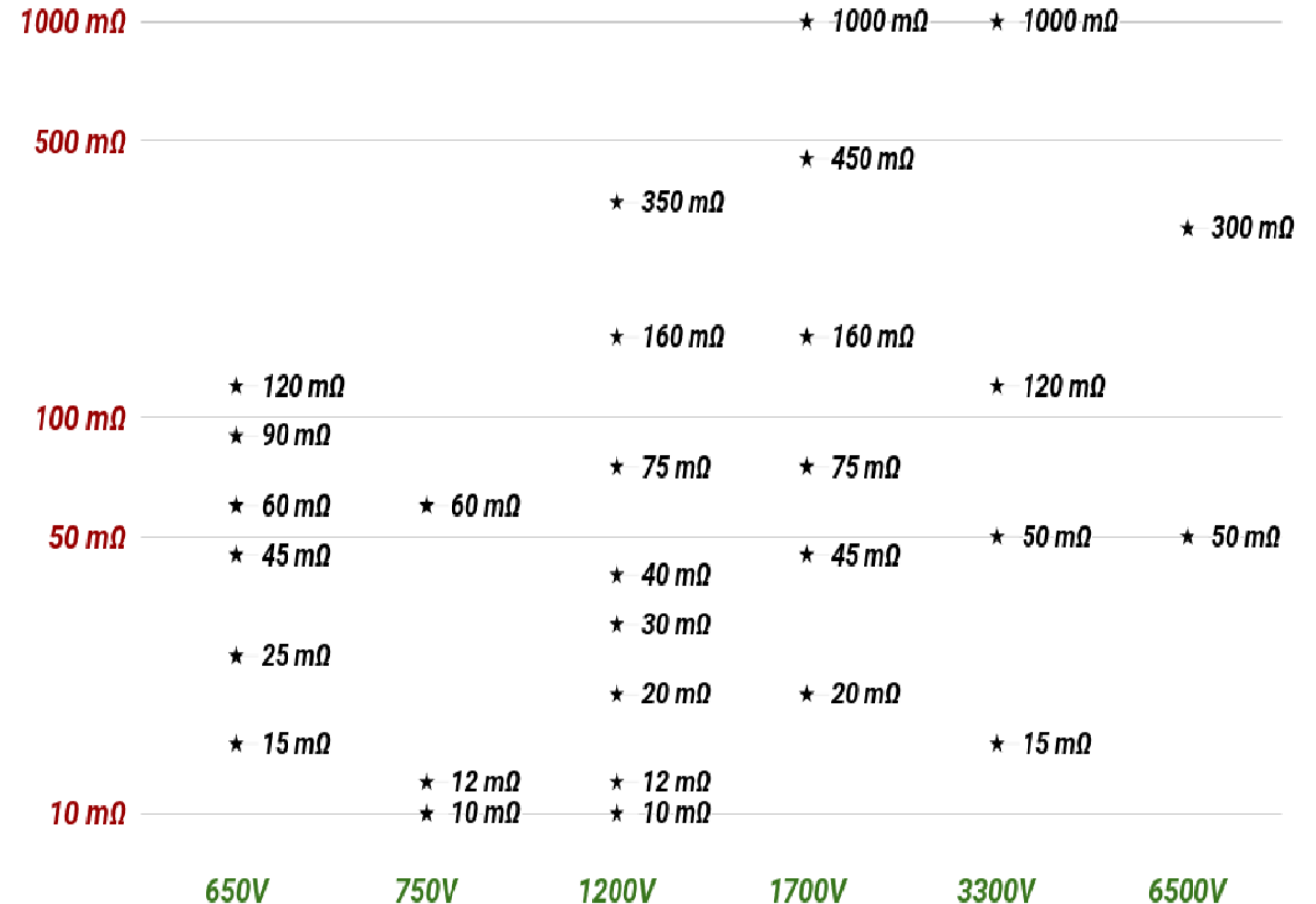
- In 2022:
 - Small share ~60k in 5 million/year
 - 110 new models
- COP27:
 - 30% ZEV sales by 2030
 - 100% by 2040
- “Megawatt Charging System”
- SAE J3271
- Up to 3.75 MW
- 1,250 V cable

DC Fast-Charger Specifications	Passenger / LDV	HDV J3721 (non-cooled)	HDV J3721 (actively-cooled)
Power (max, kW)	350	440	3,750
Voltage (max, V)	920	1,250	1,250
Current (max, A)	500	350	3,000
Vehicle Battery (nom, V)	400 / 800	800, 1200	800, 1200
SiC Device Voltage (nom, V)	750 / 1,200	1,200 / 1,700	1,700



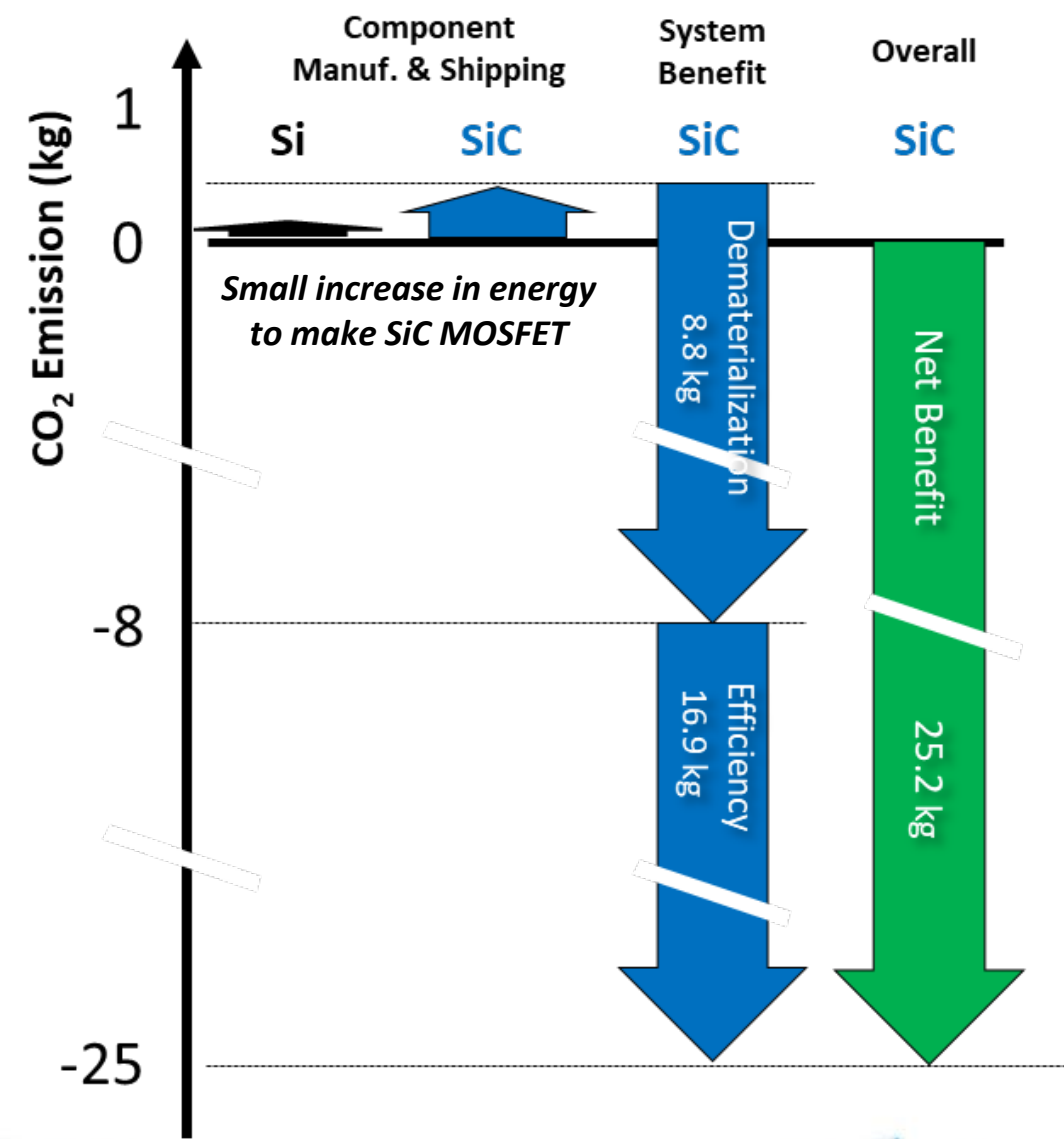
HV bus:

- Low I^2R conduction losses
- High combined motor-inverter efficiency
- Small size electric drive for same power levels
- No AC-DC conversion losses
- GeneSiC range
650V-6,500V



(1) Oak Ridge Nat. Lab. & National Renewable Energy Lab. Medium- and Heavy-Duty Vehicle Electrification: An Assessment of Technology and Knowledge Gaps (December 2019) ORNL/SPR-2020/7

Every GeneSiC MOSFET Shipped Saves Over 25 kg CO₂

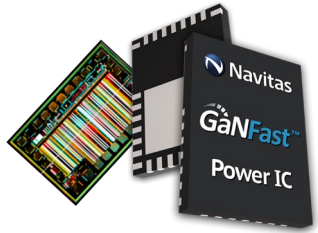


Huge benefit in application use

Every **GaNFast™** IC

saves

4 kg CO₂



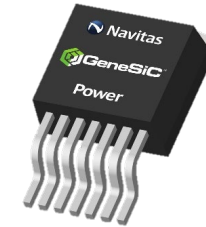
>50 GWh energy savings
Saved >225 metric tons of CO₂

GaN + SiC save
6 Gton / year by 2050

Every **GeneSiC™** FET

saves

25 kg CO₂



May '22 World's first semiconductor company
CarbonNeutral® certified



August '22 First 100,000 tons CO₂ saved
(Over 200,000 as of November 2023)



October '22 Recognized for industry-leading
sustainability reporting

Discover more
at



Wechat



Weibo

